



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

# AMMC-6241

## 26–43 GHz Low Noise Amplifier

**AVAGO**  
TECHNOLOGIES

## Data Sheet



Chip Size: 1900 x 800 mm (74.8 x 31.5 mils)  
Chip Size Tolerance: ± 10 mm ( $\pm 0.4$  mils)  
Chip Thickness: 100 ± 10 mm (4 ± 0.4 mils)  
RF Pad Dimensions: 110 x 90 mm (4.3 x 3.5 mils)  
DC Pad Dimensions: 100 x 100 mm (3.9 x 3.9 mils)

### Description

Avago Technologies AMMC-6241 is a high gain, low-noise amplifier that operates from 26 GHz to 43 GHz. This LNA provides a wide-band solution for system design since it covers several bands, thus, reduces part inventory. The device has input / output match to 50 Ohm, is unconditionally stable and can be used as either primary or sub-sequential low noise gain stage. By eliminating the complex tuning and assembly processes typically required by hybrid (discrete-FET) amplifiers, the AMMC-6241 is a cost-effective alternative in the 26 - 43 GHz communications receivers. The backside of the chip is both RF and DC ground. This helps simplify the assembly process and reduces assembly related performance variations and costs. It is fabricated in a PHEMT process to provide exceptional noise and gain performance. For improved reliability and moisture protection, the die is passivated at the active areas.

### AMMC-6241 Absolute Maximum Ratings<sup>[1]</sup>

Symbol	Parameters/Conditions	Units	Min.	Max.
V <sub>d</sub>	Positive Drain Voltage	V	7	
V <sub>g</sub>	Gate Supply Voltage	V	NA	
I <sub>d</sub>	Drain Current	mA	100	
P <sub>in</sub>	CW Input Power	dBm	15	
T <sub>ch</sub>	Operating Channel Temp.	°C	+150	
T <sub>stg</sub>	Storage Case Temp.	°C	-65	+150
T <sub>max</sub>	Maximum Assembly Temp (60 sec max)	°C		+300

Note: Operation in excess of any one of these conditions may result in permanent damage to this device.

### Features

- Wide frequency range: 26 - 43 GHz
- High gain: 20 dB
- Low 50 Ω Noise Figure: 2.7 dB
- 50 Ω Input and Output Match
- Flat Gain Response
- Single 3V Supply Bias

### Applications

- Microwave Radio systems
- Satellite VSAT, DBS Up/Down Link
- LMDS & Pt-Pt mmW Long Haul
- Broadband Wireless Access (including 802.16 and 802.20 WiMax)
- WLL and MMDS loops



Note: These devices are ESD sensitive. The following precautions are strongly recommended. Ensure that an ESD approved carrier is used when dice are transported from one destination to another. Personal grounding is to be worn at all times when handling these devices.

For more details, refer to Avago Technologies Application Note A004R:  
Electrostatic Discharge Damage and Control.  
ESD Machine Model (Class A)  
ESD Human Body Model (Class C)

## AMMC-6241 DC Specifications/Physical Properties [1]

Symbol	Parameters and Test Conditions	Units	Min.	Typ.	Max.
$I_d$	Drain Supply Current (under any RF power drive and temperature) ( $V_d=3.0\text{ V}$ )	mA	60	80	
$\theta_{ch-b}$	Thermal Resistance <sup>[2]</sup> (Backside temperature, $T_b = 25^\circ\text{C}$ )	°C/W		25	

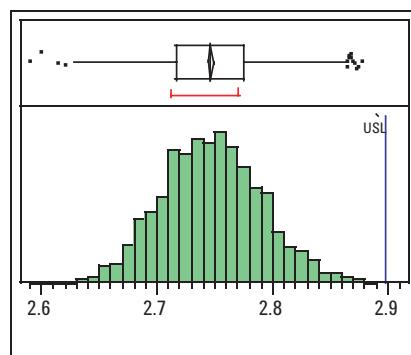
## AMMC-6241 RF Specifications [3, 4, 5]

$T_A = 25^\circ\text{C}$ ,  $V_d=3.0\text{ V}$ ,  $I_d(Q)=60\text{ mA}$ ,  $Z_{in}=Z_o=50\Omega$

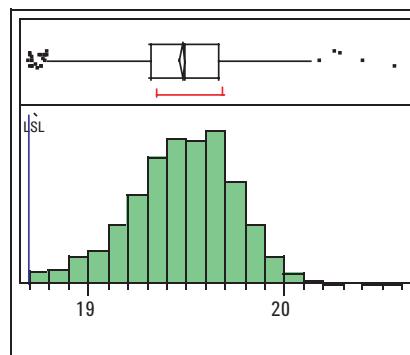
Symbol	Parameters and Test Conditions	Units	Minimum	Typical	Maximum	Sigma
Gain	Small-signal Gain <sup>[6]</sup>	dB	26-35 GHz = 20 35-40 GHz = 18.5	26-37 GHz = 21 37-40 GHz = 19.5		1.0
NF	Noise Figure into 50W	dB		26-37 GHz = 2.7 37-40 GHz = 3.0	26-37 GHz = 3.0 37-40 GHz = 3.3	0.05
P <sub>-1dB</sub>	Output Power at 1dB Gain Compression	dBm		+10		
OIP3	Third Order Intercept Point; $Df=100\text{MHz}$ ; $Pin=-35\text{dBm}$	dBm		+20		
RLin	Input Return Loss <sup>[6]</sup>	dB		-13	-11	0.40
RLOut	Output Return Loss <sup>[6]</sup>	dB		-16	-12	0.50
Isol	Reverse Isolation <sup>[6]</sup>	dB		-40		0.50

### Notes:

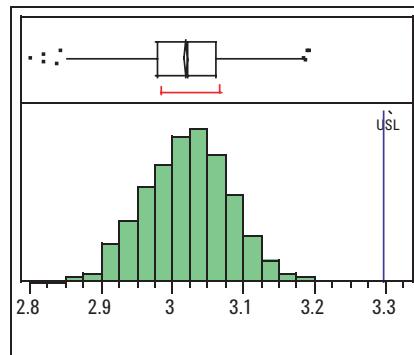
1. Ambient operational temperature  $T_A=25^\circ\text{C}$  unless otherwise noted.
2. Channel-to-backside Thermal Resistance ( $\theta_{ch-b}$ ) =  $26^\circ\text{C}/\text{W}$  at  $T_{channel}$  ( $T_c$ ) =  $34^\circ\text{C}$  as measured using infrared microscopy. Thermal Resistance at backside temperature ( $T_b$ ) =  $25^\circ\text{C}$  calculated from measured data.
3. Small/Large -signal data measured in wafer form  $T_A = 25^\circ\text{C}$ .
4. 100% on-wafer RF test is done at frequency =30, 32, and 38 GHz.
5. Specifications are derived from measurements in a  $50\Omega$  test environment. Aspects of the amplifier performance may be improved over a more narrow bandwidth by application of additional conjugate, linearity, or low noise ( $G_{opt}$ ) matching.
6. As derived from measured s-parameters



Noise Figure at 32 GHz



Gain at 38 GHz



Noise Figure at 38GHz

Typical distribution of Small Signal Gain, Noise Figure, and Return Loss. Based on 1500 part sampled over several production lots.

## AMMC-6241 Typical Performances

( $T_A = 25^\circ\text{C}$ ,  $V_{d1} = V_{d2} = 3.0 \text{ V}$ ,  $I_{\text{total}} = 60 \text{ mA}$ ,  $Z_{\text{in}} = Z_{\text{out}} = 50 \Omega$  unless otherwise stated)

NOTE: These measurements are in a  $50 \Omega$  test environment. Aspects of the amplifier performance may be improved over a narrower bandwidth by application of additional conjugate, linearity, or low noise ( $G_{\text{opt}}$ ) matching.

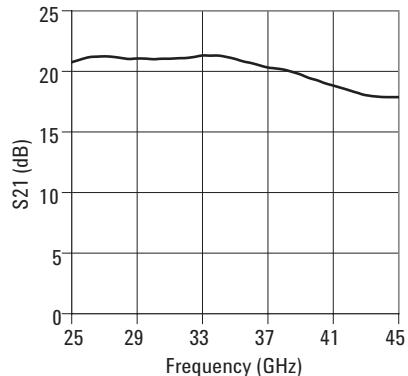


Figure 1. Typical Gain

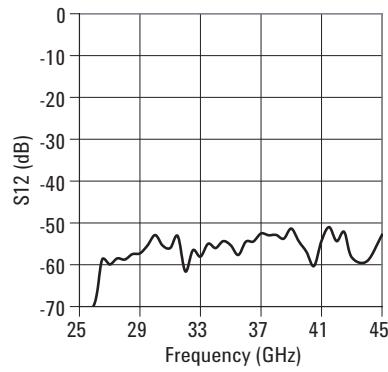


Figure 2. Typical Isolation

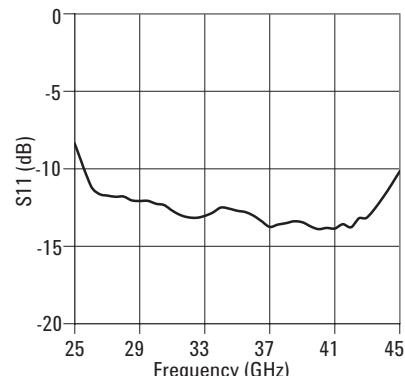


Figure 3 Typical Input Return Loss

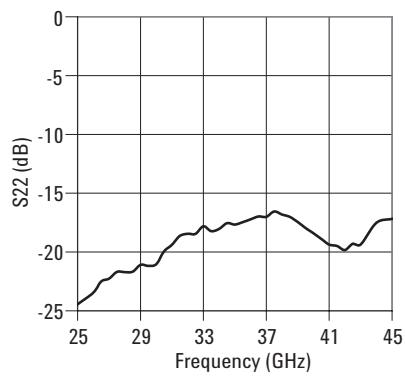


Figure 4. Typical Output Return Loss

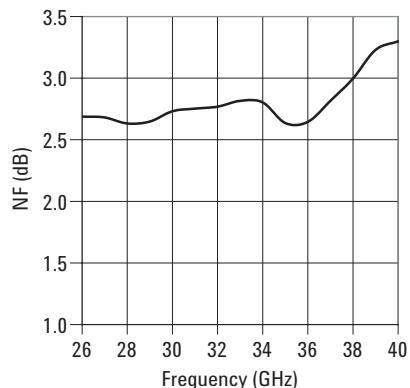


Figure 5. Typical Noise Figure into a  $50 \Omega$  load.

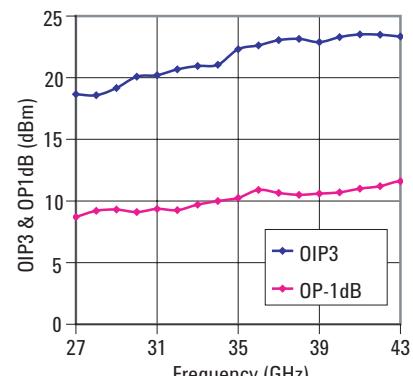


Figure 6. Typical Output  $P_{-1\text{dB}}$  and 3<sup>rd</sup> Order Intercept Point.

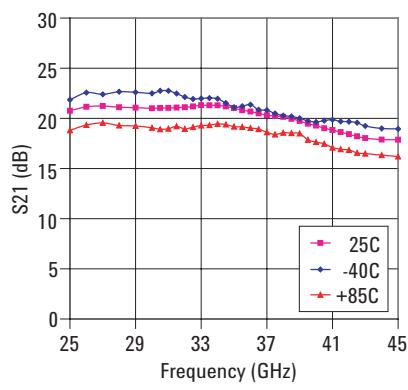


Figure 7. Gain Over Temperature

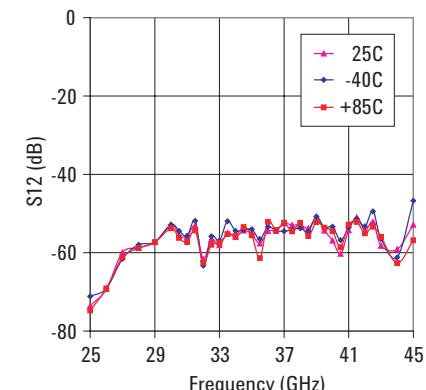


Figure 8. Isolation Over Temperature

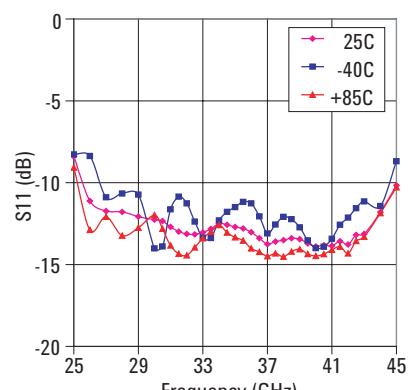


Figure 9. Input Return Loss Over Temperature

## AMMC-6241 Typical Performances

( $T_A = 25^\circ\text{C}$ ,  $V_{d1} = V_{d2} = 3.0 \text{ V}$ ,  $I_{\text{total}} = 60 \text{ mA}$ ,  $Z_{\text{in}} = Z_{\text{out}} = 50 \Omega$  unless otherwise stated)

NOTE: These measurements are in a 50 W test environment. Aspects of the amplifier performance may be improved over a narrower bandwidth by application of additional conjugate, linearity, or low noise (Gopt) matching.

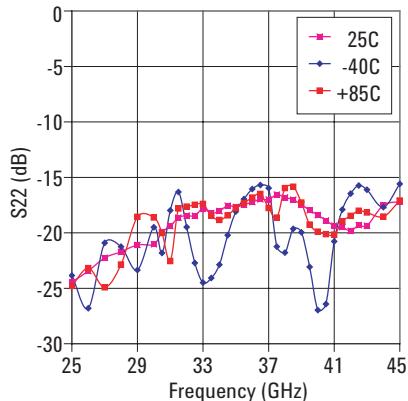


Figure 10. Output Return Loss Over Temperature

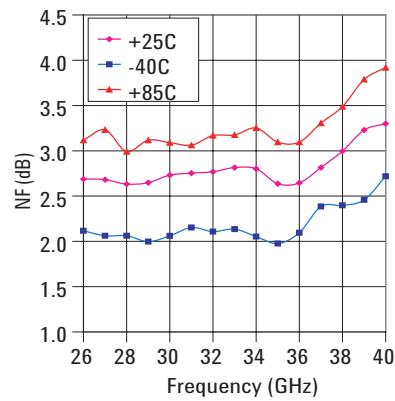


Figure 11. Noise Figure Over Temperature

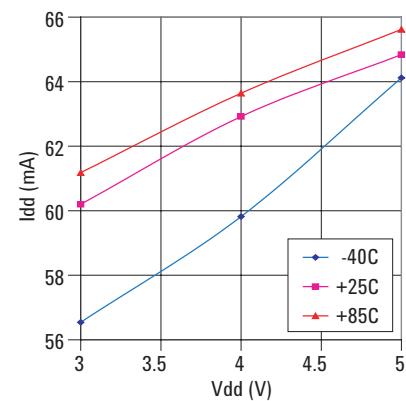


Figure 12. Typical Total Idd over Temperature

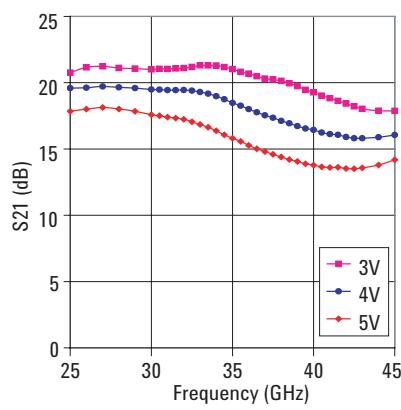


Figure 13. Gain over Vdd

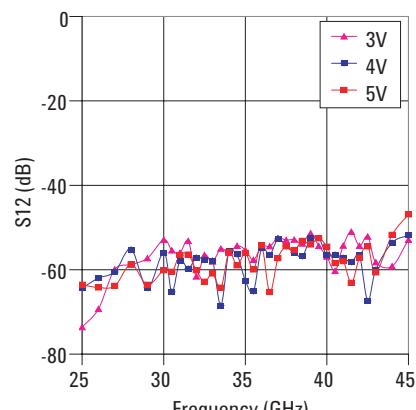


Figure 14. Isolation Over Vdd

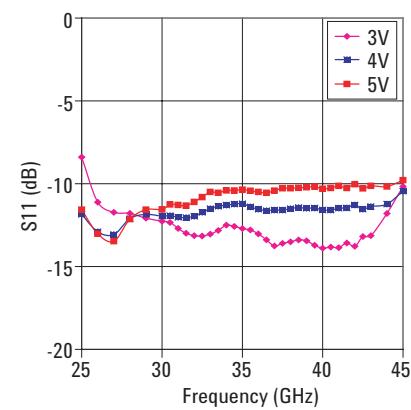


Figure 15. Input RL Over Vdd

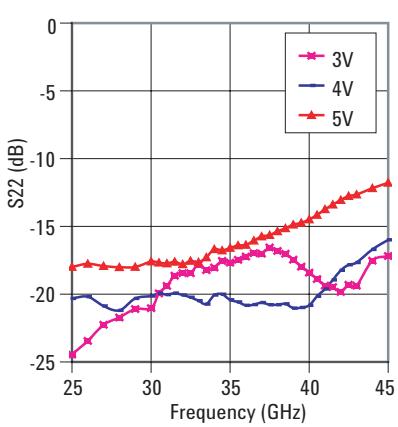


Figure 16. Output RL Over Vdd

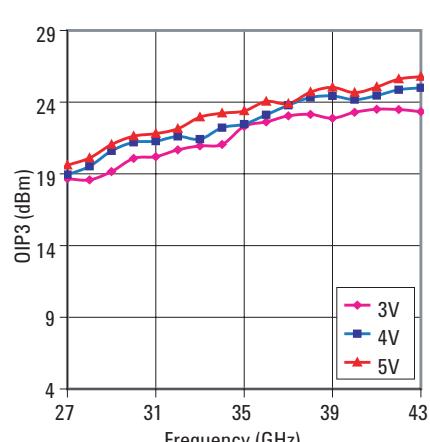


Figure 17. Output IP3 Over Vdd





## Biassing and Operation

The AMMC-6241 is normally biased with a positive supply connected to both  $V_{D1}$  and  $V_{D2}$  bond pads through the 100pF bypass capacitor as shown in Figure 21. The recommended supply voltage is 3 V. It is important to place the bypass capacitor as close to the die as possible. No negative gate bias voltage is needed for the AMMC-6241. Input and output matching are achieved on-die, therefore no other external component is required besides one 100pF bypass capacitor for the main supply. The input and output are DC-blocked with internal coupling capacitors.

No ground wires are needed because all ground connections are made with plated through-holes to the backside of the device.

Refer the Absolute Maximum Ratings table for allowed DC and thermal conditions.

## Assembly Techniques

The backside of the MMIC chip is RF ground. For microstrip applications the chip should be attached directly to the ground plane (e.g. circuit carrier or heatsink) using electrically conductive epoxy<sup>[1,2]</sup>.

For best performance, the topside of the MMIC should be brought up to the same height as the circuit surrounding it. This can be accomplished by mounting a gold plate metal shim (same length and width as the MMIC) under the chip which is of correct thickness to make the chip and adjacent circuit the same height. The amount of epoxy used for the chip and/or shim attachment should

be just enough to provide a thin fillet around the bottom perimeter of the chip or shim. The ground plan should be free of any residue that may jeopardize electrical or mechanical attachment.

The location of the RF bond pads is shown in Figure 12. Note that all the RF input and output ports are in a Ground-Signal-Ground configuration.

RF connections should be kept as short as reasonable to minimize performance degradation due to undesirable series inductance. A single bond wire is normally sufficient for signal connections, however double bonding with 0.7 mil gold wire or use of gold mesh is recommended for best performance, especially near the high end of the frequency band.

Thermosonic wedge bonding is preferred method for wire attachment to the bond pads. Gold mesh can be attached using a 2 mil round tracking tool and a tool force of approximately 22 grams and a ultrasonic power of roughly 55 dB for a duration of 76 +/- 8 mS. The guided wedge at an ultrasonic power level of 64 dB can be used for 0.7 mil wire. The recommended wire bond stage temperature is 150 +/- 2C.

Caution should be taken to not exceed the Absolute Maximum

Notes:

1. Ablebond 84-1 LM1 silver epoxy is recommended.
2. Eutectic attach is not recommended and may jeopardize reliability of the device.

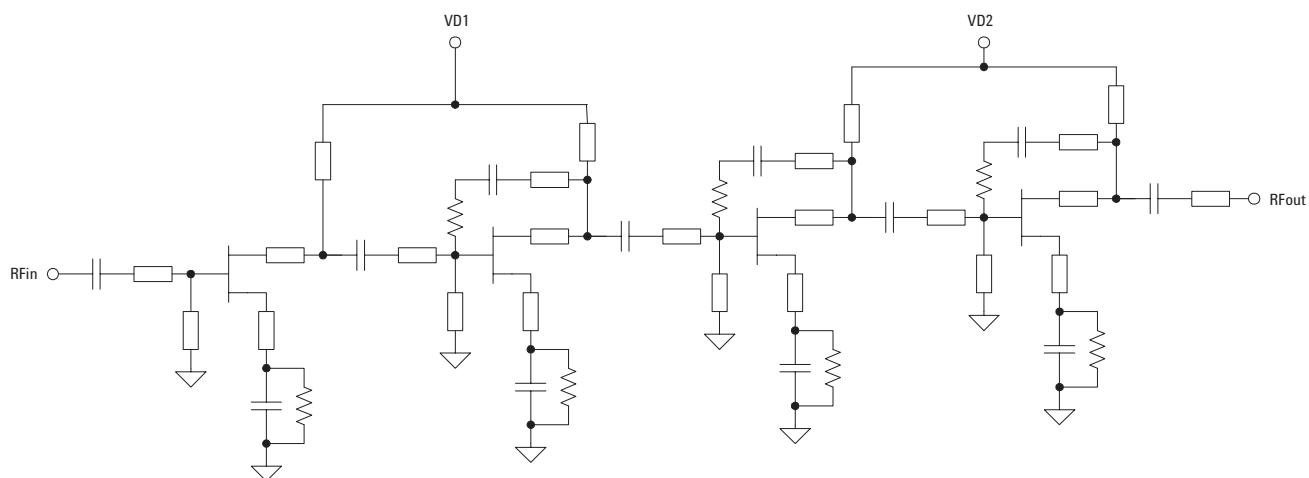


Figure 18. AMMC-6241 Simplified Schematic

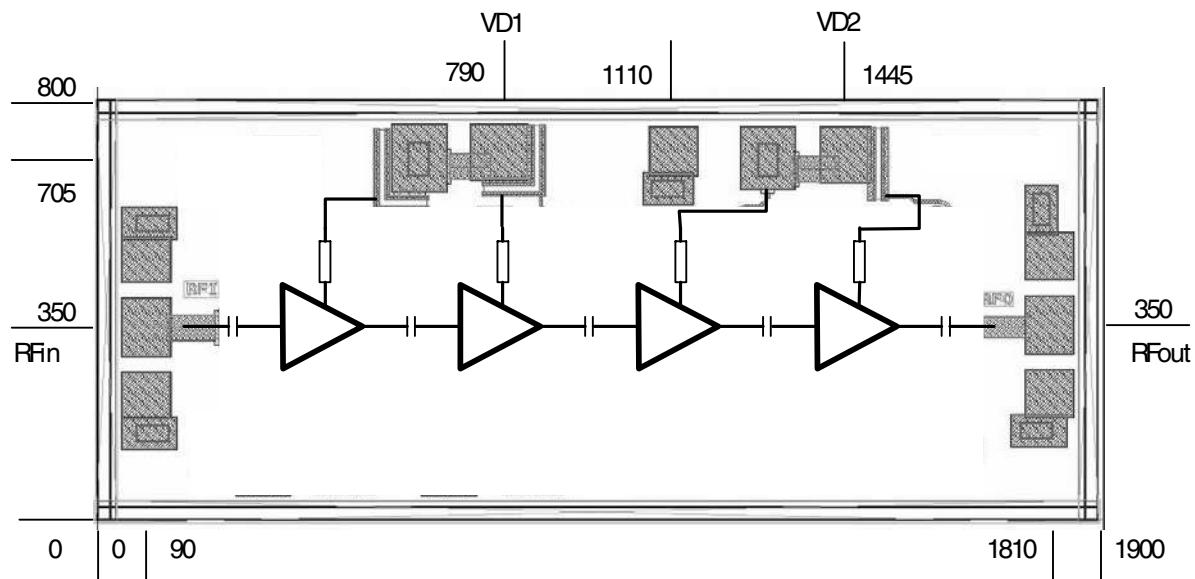


Figure 19. AMMC-6241 Bonding pad locations

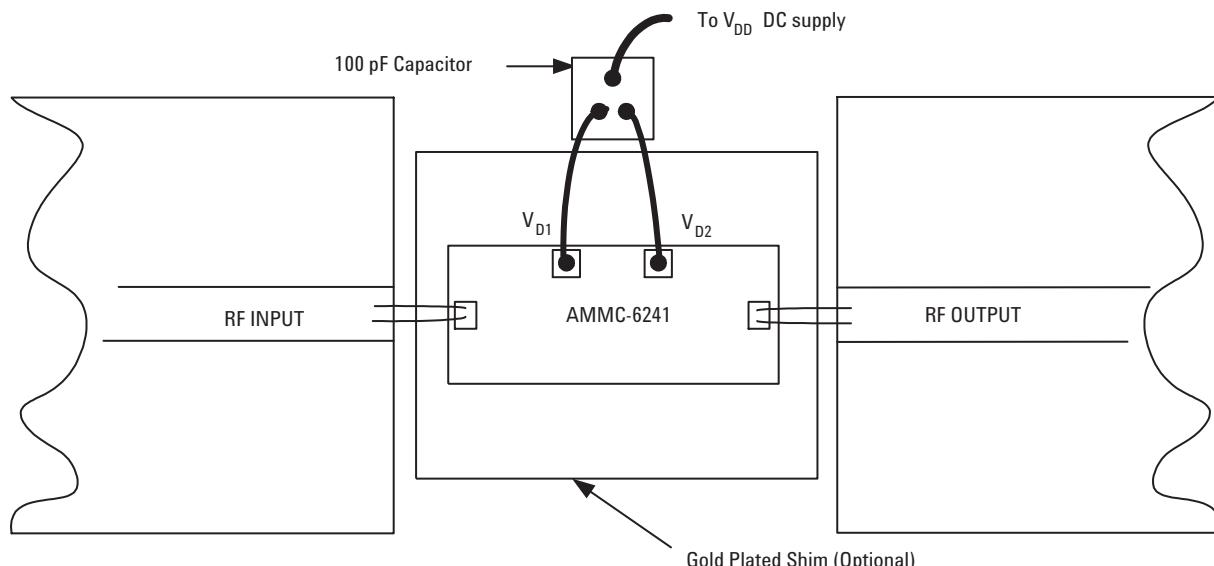


Figure 20. AMMC-6241 Assembly diagram

#### Ordering Information:

AMMC-6241-W10 = 10 devices per tray

AMMC-6241-W50 = 50 devices per tray

For product information and a complete list of distributors, please go to our web site: [www.avagotech.com](http://www.avagotech.com)

Avago, Avago Technologies, and the A logo are trademarks of Avago Technologies Limited in the United States and other countries.  
Data subject to change. Copyright © 2005-2008 Avago Technologies Limited. All rights reserved. Obsoletes AV01-0231EN  
AV02-13xxEN - June 23, 2008